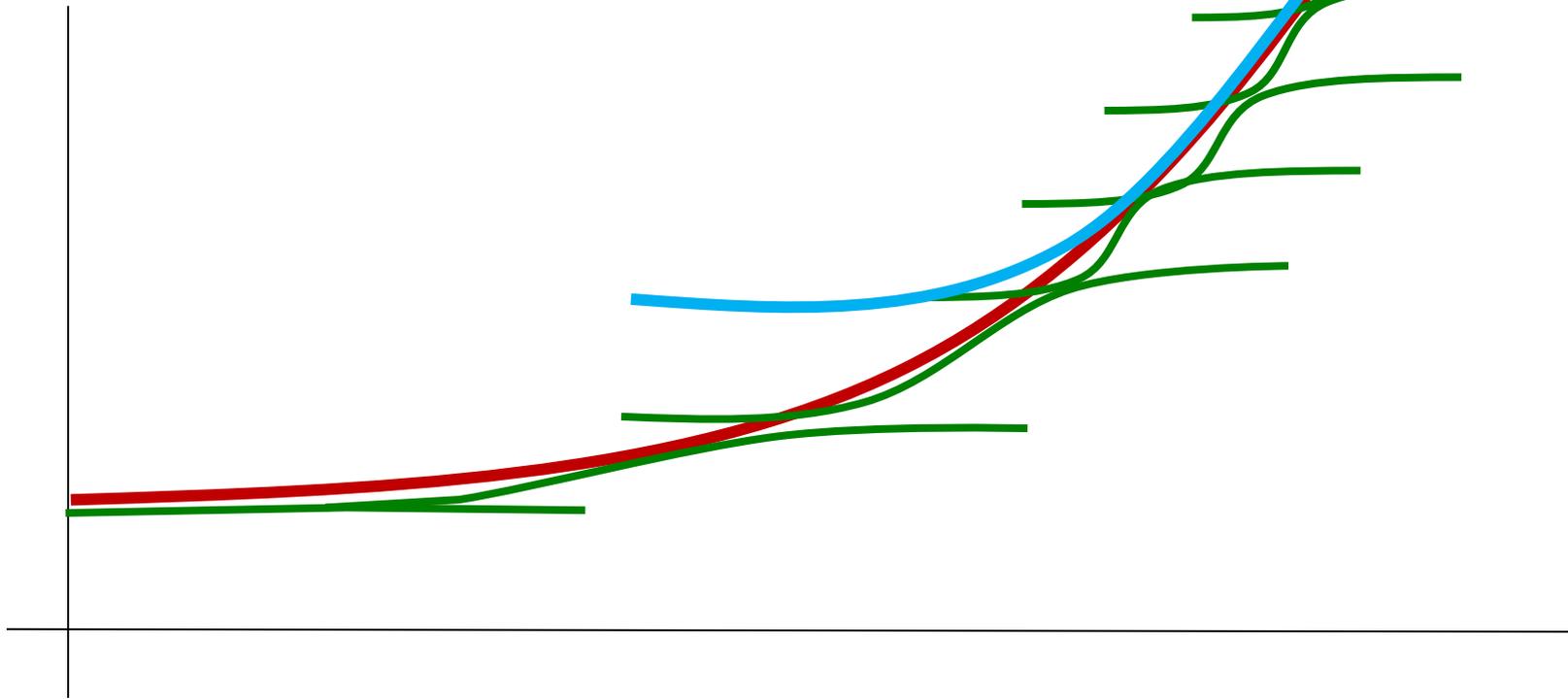


SPIE Advanced Lithography 2011 paper 7970-1

# e-Beam Direct Write of Wafers

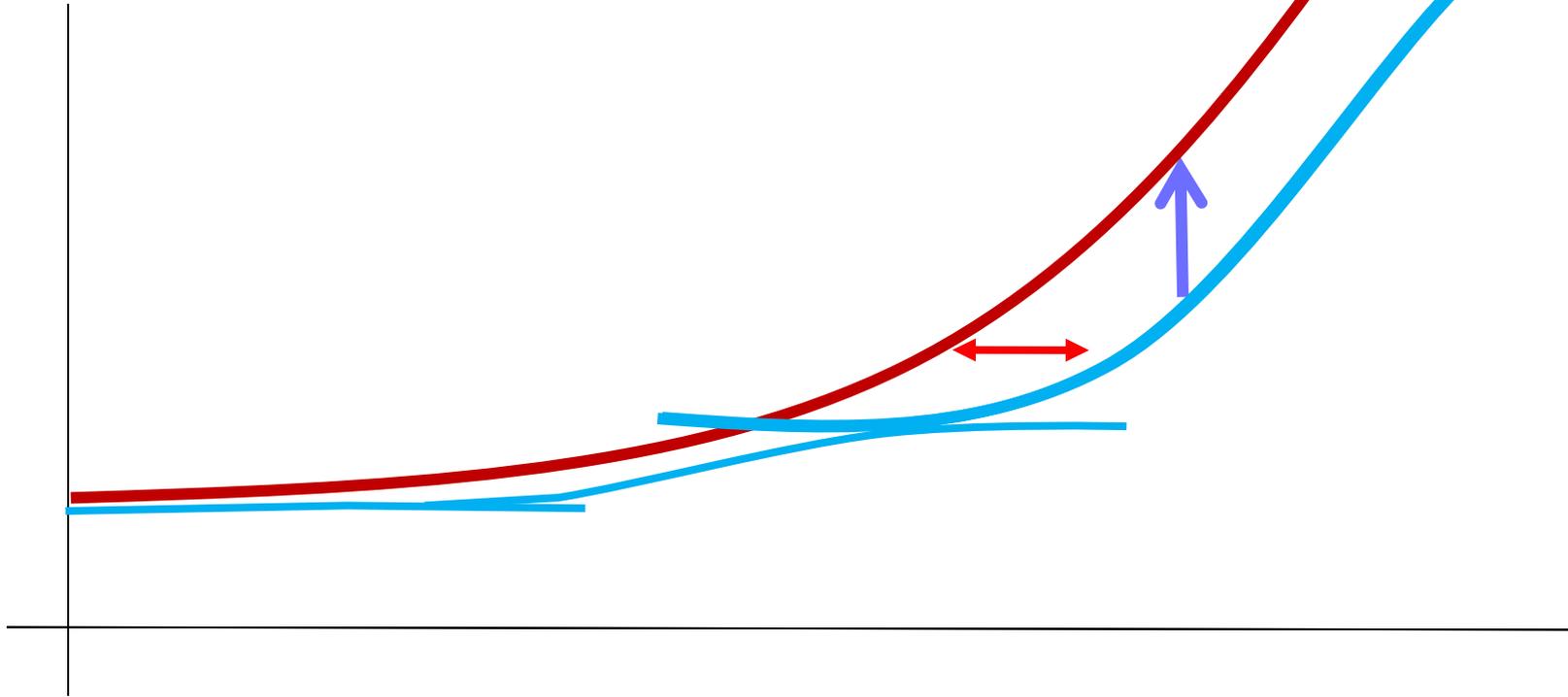
Aki Fujimura, D<sub>2</sub>S, Inc

# What you do is amazing! *Making S-Curves fit a Geometric*



If you have small S-Curves, you have to stack them one after another  
If you are blessed with a big S-Curve, you get to ride it for a long time

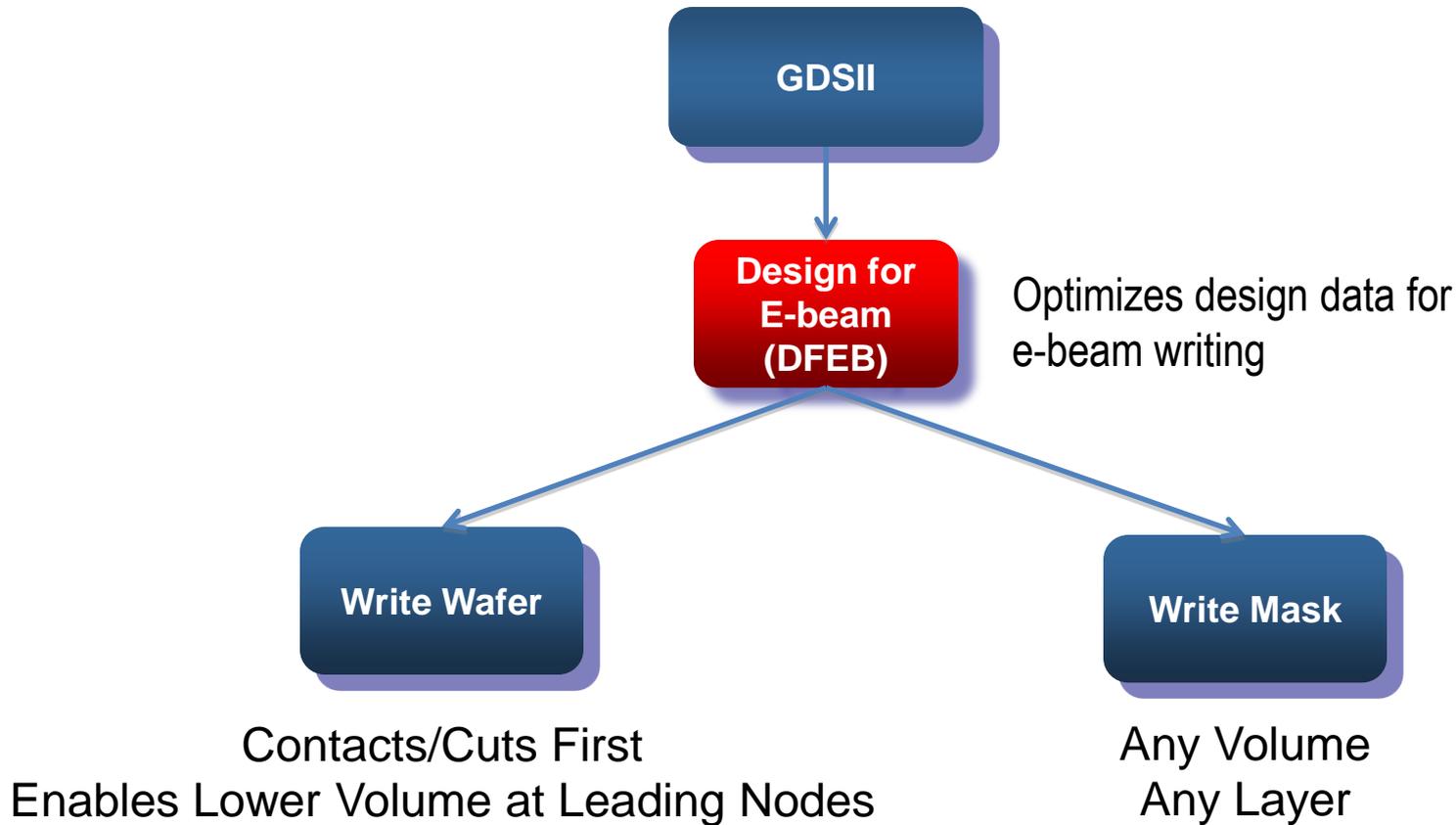
“EbDW is always 1-2 generations behind”



But that means it HAS kept up with Moore's Law... Just needs to catch up

# Direct-Write or Mask?

## Either Way, e-Beam Writes All Chips!

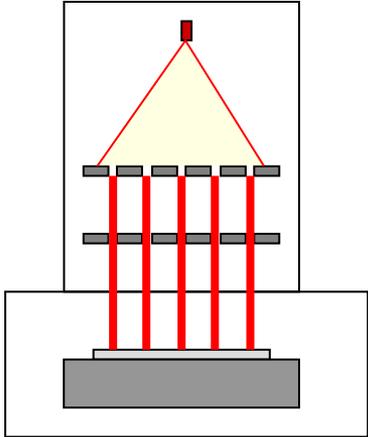
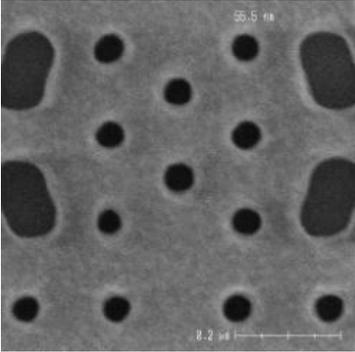


# Similar but different...

Need	Mask	Wafer
Size	4x	1x
Accuracy	Highest (MEEF)	High (less source of error)
Data volume	Huge (SRAF)	Huge x 10 (no OPC; whole wafer)
Write Time	8-40 hours	1 ~ 100 WPH
Writing Space	Rectangle (efficient)	Circle (inefficient)
# passes	2, 4 (accuracy)	1 (write time)
Characters	Circles	1000's useful
Market now	Solid but flat	Zero but big potential

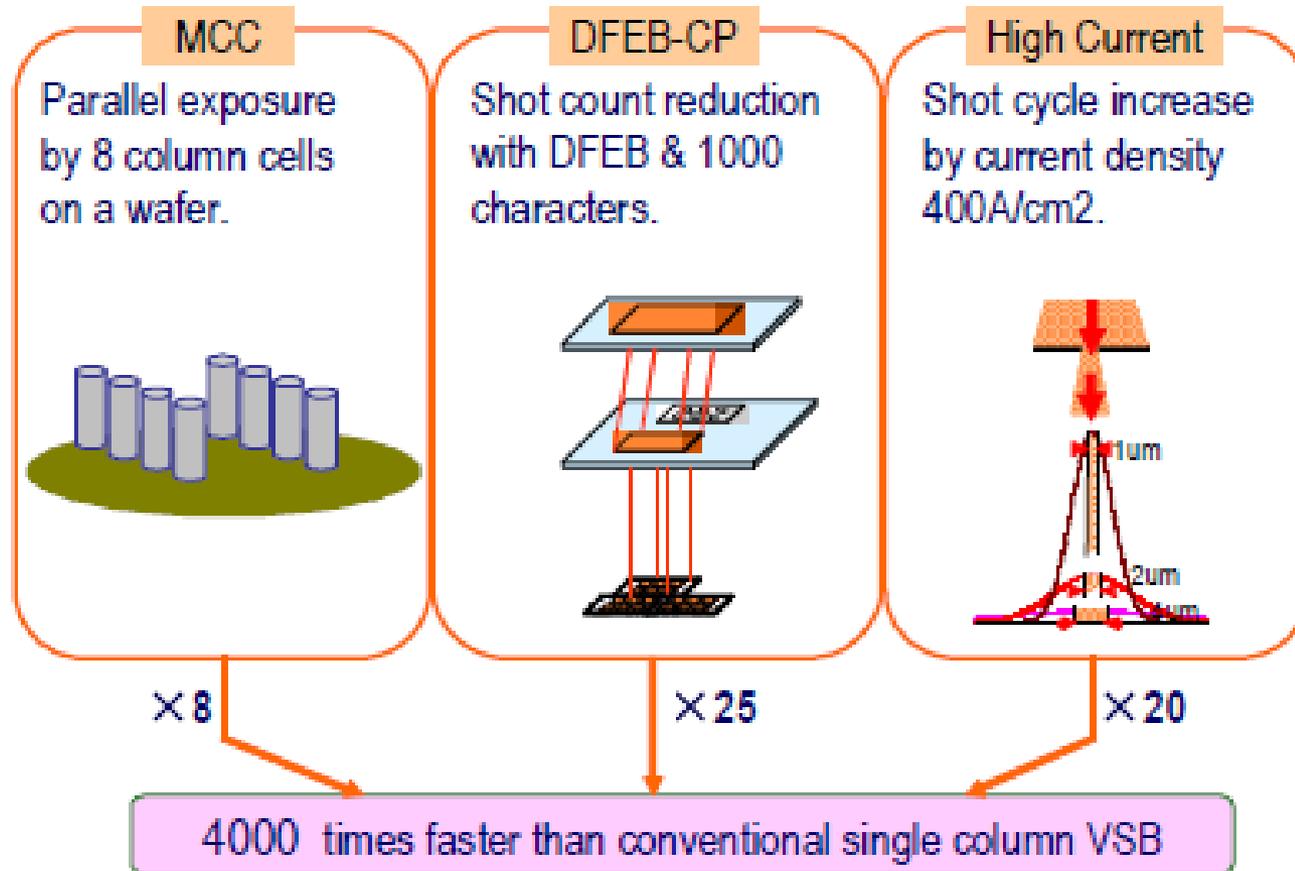
NIL Mask Master is a blend of both

# eBeam Speed-Up techniques

Split Beam	Character Proj.	General
 <p data-bbox="629 715 749 762"><b>MSB</b></p>		<p data-bbox="1367 386 1740 436">Multiple Source</p> <p data-bbox="1431 462 1676 512">Clustering</p> <p data-bbox="1367 538 1740 588">Source Current</p> <p data-bbox="1350 614 1758 664">Resist Sensitivity</p> <p data-bbox="1292 689 1816 739">Regular Design Rules</p> <p data-bbox="1315 765 1792 815">Borodovsky Method</p> <p data-bbox="1406 841 1702 891"><i>Other Limits:</i></p> <p data-bbox="1483 916 1624 966">Stage</p> <p data-bbox="1392 992 1715 1042">Data Transfer</p> <p data-bbox="1425 1068 1682 1118">Calibration</p> <p data-bbox="1363 1143 1734 1193">Settling Time ...</p>
<p data-bbox="88 868 672 918">DFEB = Data Compression</p>	<p data-bbox="730 868 1219 918">DFEB = 10X Speed-up</p>	
<p data-bbox="127 1029 633 1139">Maximum flexibility in shape being written</p>	<p data-bbox="726 1029 1224 1139">Maximum transfer of energy for all shapes</p>	

# Advantest MCC8

*Realistic with limited budget is to extend*



X 10 Cluster

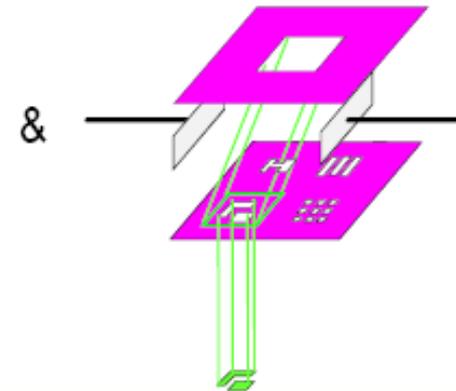
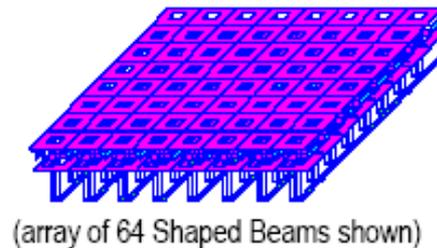
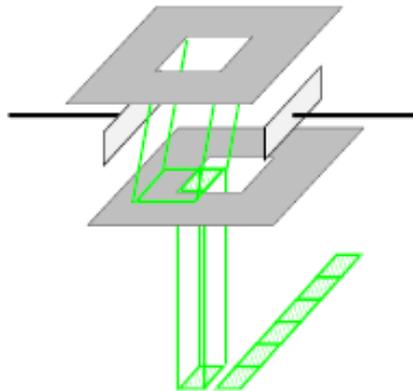
# Vistec MSB

*Hybrid like Prius is the best way to transition*

Single  
Variable Shaped Beam



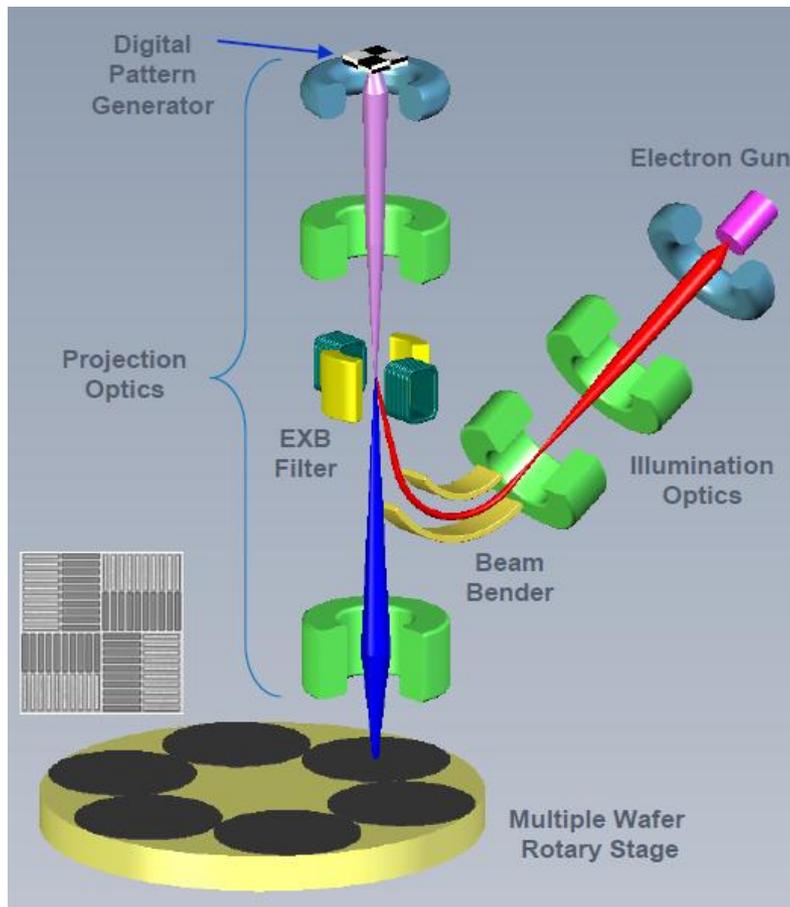
Vistec's Multi Shaped Beam approach:  
MSB technology &  
single VSB including Cell Projection



MSB maintains the parallel pixel exposure advantage of shaped beams (average >100 pixels / beamlet) resulting in thousands of pixels per flash.

# IMS, KLA-T REBL, Mapper, Multibeam

## *Take on the bigger S-Curve*



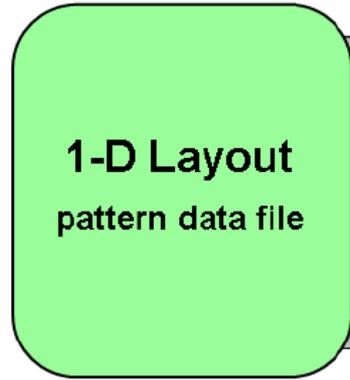
Multiple beams individually controlled by various means

Innovation in stage, data pipeline and column taken as a system

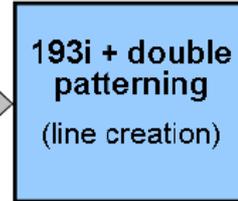
Expensive but worth it

# Design to Manufacturing collaboration

*Focus to succeed : The “Borodovsky method”*



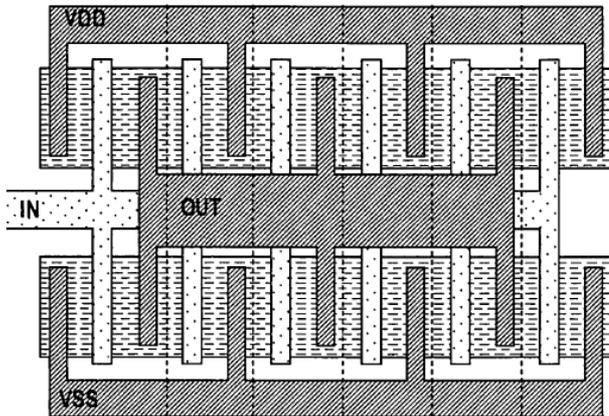
Lines



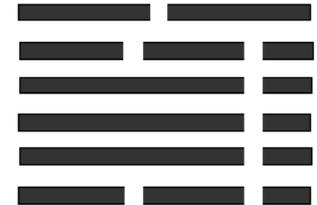
Line-Cuts



Design for E-Beam (DFEB)



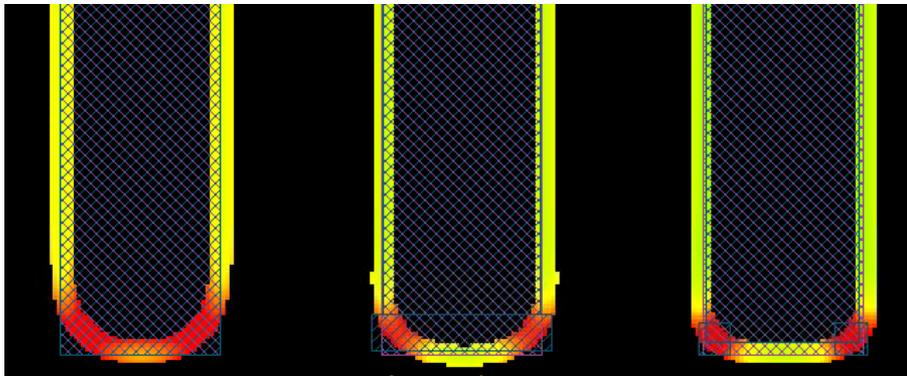
Final pattern combining lines and “cuts”



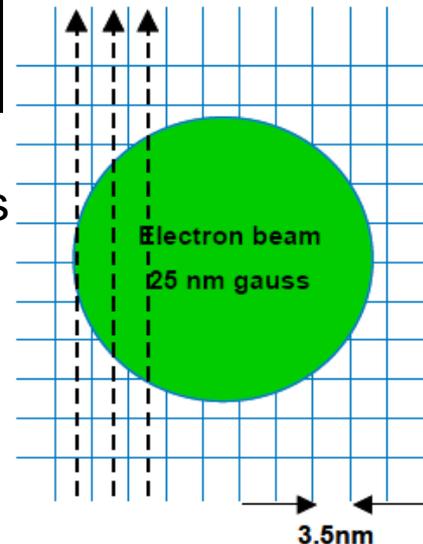
# ASELTA, CEA/Leti, D2S, EQUIcon, Fraunhofer, Technolution, TSMC

*Software help is essential for this resolution*

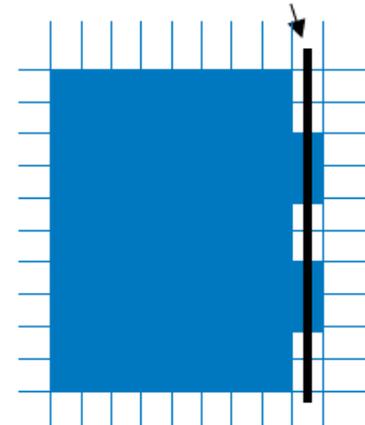
MB-MDP on 80nm L:S for mask



Mapper data prep for 3.5nm resolution



Example (line edge biasing):  
edge position 1/2 pixel shifted



Even eBeam writing is hard at these nodes

- MB-MDP
- MPC
- eRIF
- EBPC

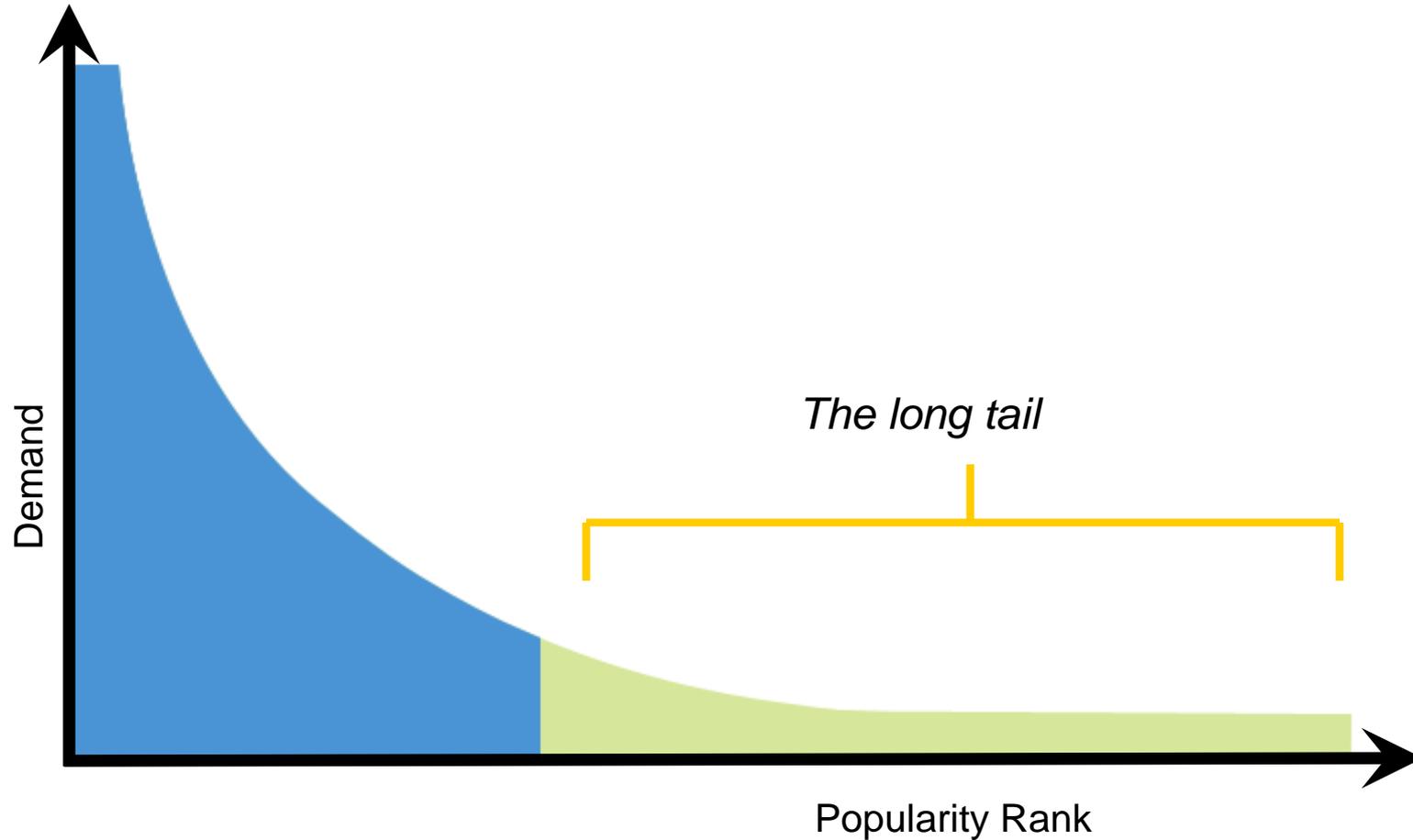
# Themes and Approaches

*EbDW : we can do this....*

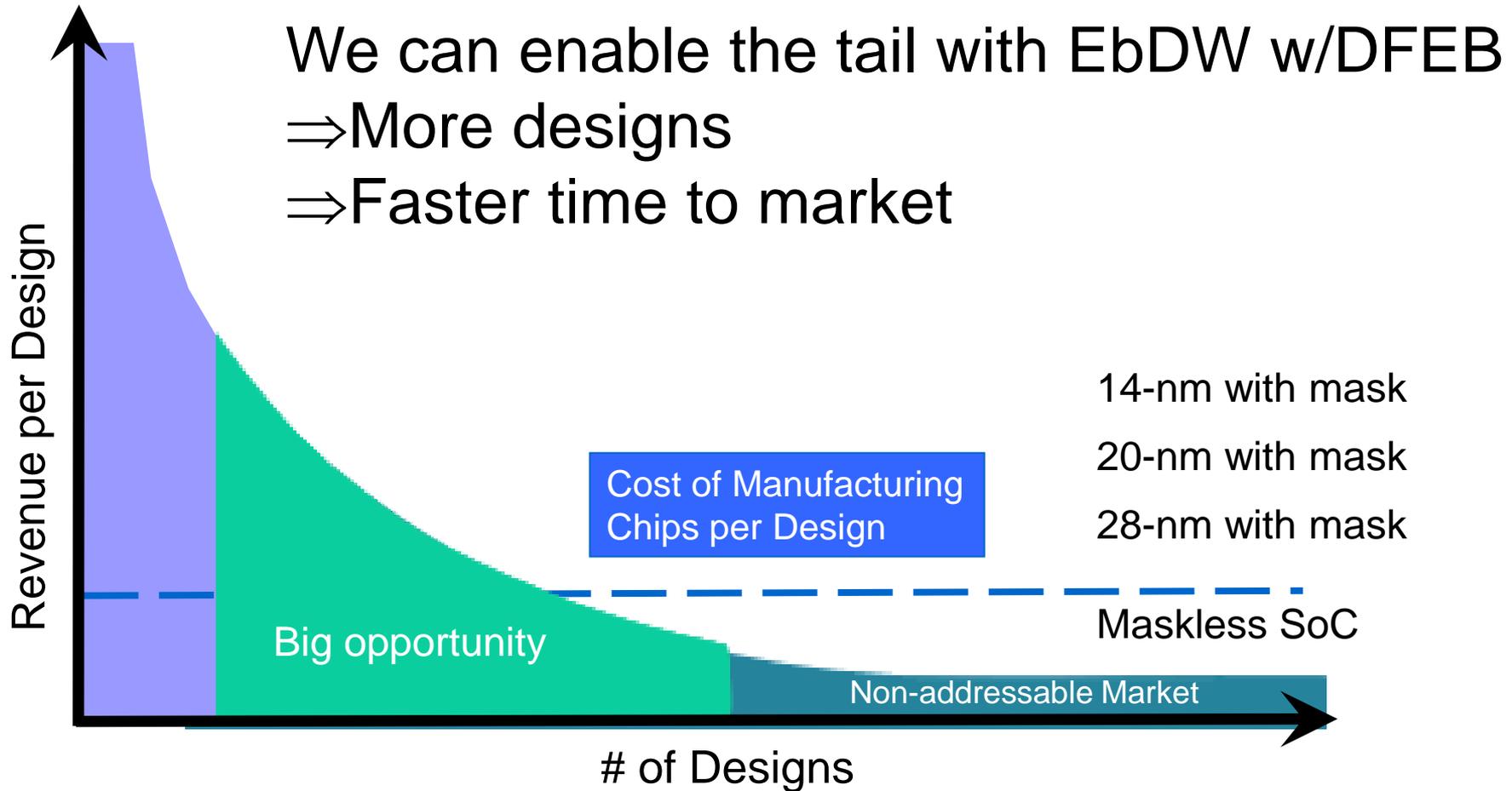


- **Monetize from the Existing Mask Market**
  - D2S, IMS, SEMATECH, Vistec
  - “Current density advances will not be enough” – Tom Faure, IBM
- **EbDW for high volume with clusters**
- **EbDW can also enable the long tail**
- **Government funding is deserved**
  - EbDW will help boost design starts
  - That’s good for everyone in the supply chain

# Enabling the Long Tail of SoCs

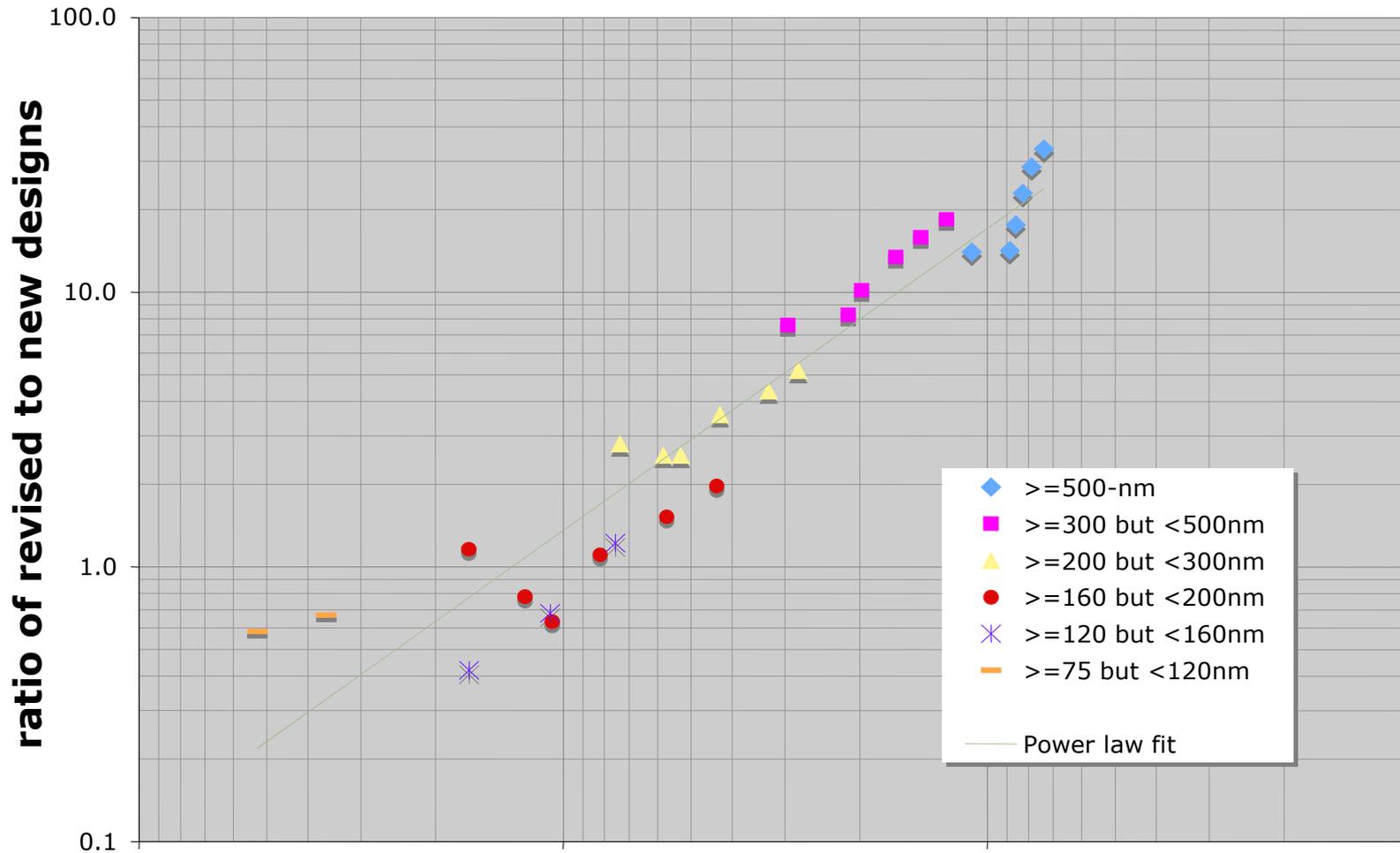


# The Tail is Getting Shorter



# Derivatives have low design cost

10x reduction in mask cost increases derivatives by 10x



# Electron Beam Direct Write

- Great for R&D : process, design, systems
- Great for lower-volume : minimal mask cost
- Volume Production? : 50 WPH cluster in 2014
  
- Please attend these great sessions and learn about the potential of e-beam technologies

## Session 3: Maskless Lithography I

Date: **Tuesday 1 March** Time: **1:20 PM - 3:10 PM**

Session Chairs: [Hans Loeschner](#), IMS Nanofabrication AG (Austria);  
[Timothy R. Groves](#), Univ. at Albany



### **E-beam lithography development, outlook, and critical challenges** *(Invited Paper)*

Paper 7970-9 Time: **1:20 PM - 1:50 PM**

Author(s): Hans C. Pfeiffer, HCP Consulting Services (United States)

### **MCC8: throughput enhancement of EB direct writer**

Paper 7970-10 Time: **1:50 PM - 2:10 PM**

Author(s): Hideaki Komami, Masaki Kurokawa, Akio Yamada, Advantest Corp. (Japan)

### **eMET: 50 keV electron multibeam mask exposure tool**

Paper 7970-11 Time: **2:10 PM - 2:30 PM**

Author(s): Christof Klein, Jan Klikovits, Hans Loeschner, Elmar Platzgummer, IMS Nanofabrication AG (Austria)

### **Scanning exposures with a MAPPER multibeam system**

Paper 7970-12 Time: **2:30 PM - 2:50 PM**

Author(s): Bert J. Kampherbeek, Christiaan van den Berg, Vincent Kuiper, Niels Vergeer, Stijn Bosschker, Thomas Ooms, Alexandra Tudorie, Remco J. Jager, MAPPER Lithography (Netherlands); Sjoerd Postma, DEMCON (Netherlands); Guido de Boer, MAPPER Lithography (Netherlands)

### **Multishaped beam: development status and update on lithography results**

Paper 7970-13 Time: **2:50 PM - 3:10 PM**

Author(s): Ines A. Stolberg, Matthias Slodowski, Hans-Joachim Doering, Wolfgang H. Dorl, Vistec Electron Beam GmbH (Germany)

## Session 8: Maskless Lithography II

Date: **Wednesday 2 March** Time: **3:30 PM - 5:40 PM**

Session Chairs: [Lloyd C. Litt](#), SEMATECH Inc.; [Laurent Pain](#), CEA-LETI (France)



### **Fast mask writer: technology options and considerations** (*Invited Paper*)

Paper 7970-32 Time: **3:30 PM - 4:00 PM**

Author(s): Lloyd C. Litt, SEMATECH Inc. (United States); Timothy R. Groves, Univ. at Albany (United States); Gregory P. Hughes, SEMATECH, Inc. (United States)

### **IMAGINE: an open consortium to boost maskless lithography take off: first assessment results on MAPPER technology**

Paper 7970-33 Time: **4:00 PM - 4:20 PM**

Author(s): Laurent Pain, Serge V. Tedesco, Beatrice Icard, Mickael Martin, Christophe Constancias, Lab. d'Electronique de Technologie de l'Information (France); Bert J. Kampherbeek, MAPPER Lithography (Netherlands)

### **Influence of massively parallel e-beam direct-write pixel size on electron proximity correction**

Paper 7970-34 Time: **4:20 PM - 4:40 PM**

Author(s): Shy-Jay Lin, Taiwan Semiconductor Manufacturing Co. Ltd. (Taiwan)

### **Data path development for massive electron-beam maskless lithography**

Paper 7970-35 Time: **4:40 PM - 5:00 PM**

Author(s): Faruk Krecinic, Jack J. Chen, Shy-Jay Lin, Burn J. Lin, Taiwan Semiconductor Manufacturing Co. Ltd. (Taiwan)

### **EBDW to complement optical lithography for 1D GDR patterning**

Paper 7970-36 Time: **5:00 PM - 5:20 PM**

Author(s): David K. Lam, David Liu, Multibeam Corp. (United States); Michael C. Smayling, Tela Innovations, Inc. (United States); Ted Prescop, Multibeam Corp. (United States)

### **Model-based mask data preparation and impact on resist heating**

Paper 7970-37 Time: **5:20 PM - 5:40 PM**

Author(s): Aki Fujimura, D2S, Inc. (United States); Takashi Kamikubo, NuFlare Technology, Inc. (Japan); Ingo Bork, D2S, Inc. (United States)

# Session 10: Maskless Lithography III

Date: **Thursday 3 March** Time: **10:20 AM - 12:10 PM**

Session Chairs: [Lloyd C. Litt](#), SEMATECH Inc.; [Hans Loeschner](#), IMS Nanofabrication AG (Austria)



## **New advances with REBL for maskless high-throughput EBDW lithography** *(Invited Paper)*

Paper 7970-43 Time: **10:20 AM - 10:50 AM**

Author(s): Paul Petric, Chris Bevis, Mark A. McCord, Allen Carroll, Alan D. Brodie, Upendra Ummethala, Luca Grella, Regina Freed, KLA-Tencor Corp. (United States)

## **Large-scale eRIF implementation for sub-22-nm e-beam lithography**

Paper 7970-44 Time: **10:50 AM - 11:10 AM**

Author(s): Luc Martin, Lab. d'Electronique de Technologie de l'Information (France); Serdar Manakli, Sébastien Bayle, ASELT Nanographics (France); Kang-Hoon Choi, Manuela S. Gutsch, Fraunhofer-Ctr. Nanoelektronische Technologien (Germany); Laurent Pain, Lab. d'Electronique de Technologie de l'Information (France)

## **Demonstration of real-time pattern correction for high-throughput maskless lithography**

Paper 7970-45 Time: **11:10 AM - 11:30 AM**

Author(s): Marco J. Wieland, Ton van de Peut, Martijn Sanderse, MAPPER Lithography (Netherlands); Edwin Hakkennes, Nol Venema, Ard Wiersma, Mark Hoving, Sijmen Woutersen, Technolution B.V. (Netherlands)

## **EBPC for multibeams low-kV electron projection lithography**

Paper 7970-46 Time: **11:30 AM - 11:50 AM**

Author(s): Jérôme Belledent, Sebastien Soulan, Laurent Pain, Commissariat à l'Énergie Atomique (France)

## **Fast characterization of line-end shortening and application of novel LES correction algorithms in e-beam direct write**

Paper 7970-47 Time: **11:50 AM - 12:10 PM**

Author(s): Martin Freitag, Manuela S. Gutsch, Kang-Hoon Choi, Christoph K. Hohle, Fraunhofer-Ctr. Nanoelektronische Technologien (Germany); Michael Krüger, EQUIcon Software GmbH Jena (Germany); Ulf Weidenmüller, Vistec Electron Beam GmbH (Germany)

## It's time to make it happen...

- **EbDW will scale, once it catches a node**
- **Need to collaborate and coordinate even more**
  - Too many teams in the league is diluting the quality and funding
  - Column, stage, data-path and integration should share
- **EbDW projects need more funding**
  - Will help boost design starts at the leading edge nodes
  - Good for everyone in the supply chain
  - Spurs more silicon innovation
  - Fuels more systems innovation



**Beam**  
**Initiative**